

# Absolute Maximum Ratings – NPN 5551 Section ( $@T_A = +25^{\circ}C$ , unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V <sub>CBO</sub>	180	V
Collector-Emitter Voltage	V <sub>CEO</sub>	160	V
Emitter-Base Voltage	V <sub>EBO</sub>	6	V
Continuous Collector Current	Ic	200	mA

## Absolute Maximum Ratings - PNP 5401 Section (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V <sub>CBO</sub>	-160	V
Collector-Emitter Voltage	V <sub>CEO</sub>	-150	V
Emitter-Base Voltage	V <sub>EBO</sub>	-6	V
Continuous Collector Current	Ic	-200	mA

#### Thermal Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit	
Dower Dissination	(Note 5)	Б	200		
Power Dissipation	(Notes 6 & 7)	$P_D$	320	mW	
Thermal Resistance, Junction to Ambient	(Note 5)	D	625	°C/W	
Thermal Resistance, Junction to Ambient	(Notes 6 & 7)	$R_{\theta JA}$	390		
Thermal Resistance, Junction to Case	(Note 8)	R <sub>θ</sub> JC	140		
Operating and Storage Temperature Range		T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C	

Notes:

<sup>5.</sup> For a device mounted on minimum recommended pad layout 1oz weight copper that is on a single-sided FR-4 PCB; device is measured under still air conditions whilst operating in a steady-state.

<sup>6.</sup> Same as Note 5, except the device is mounted on 25mm X 25mm 2oz copper.

<sup>7.</sup> Maximum combined dissipation.

<sup>8.</sup> Thermal resistance from junction to the top of package.



#### Electrical Characteristics - NPN 5551 Section (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS						
Collector-Base Breakdown Voltage	BV <sub>CBO</sub>	180			>	$I_C = 100\mu A, I_E = 0$
Collector-Emitter Breakdown Voltage (Note 9)	BV <sub>CEO</sub>	160			>	$I_C = 1 \text{mA}, I_B = 0$
Emitter-Base Breakdown Voltage	BV <sub>EBO</sub>	6			>	$I_E = 10\mu A, I_C = 0$
Collector-Base Cutoff Current	1			50	nA	$V_{CB} = 120V, I_{E} = 0$
Collector-Base Cuton Current	I <sub>CBO</sub>		_	50	μA	$V_{CB} = 120V, I_E = 0, T_A = +100^{\circ}C$
Base-Emitter Cutoff Current	I <sub>EBO</sub>		_	50	nA	$V_{EB} = 4V, I_{C} = 0$
ON CHARACTERISTICS (Note 9)						
	h <sub>FE</sub>	80			_	$I_C = 1.0 \text{mA}, V_{CE} = 5.0 \text{V}$
DC Current Gain		80	_	250		$I_C = 10mA, V_{CE} = 5.0V$
		30		_		$I_C = 50 \text{mA}, V_{CE} = 5.0 \text{V}$
Collector-Emitter Saturation Voltage	V	CE(SAT) —	_	0.15	<u> </u>	I <sub>C</sub> = 10mA, I <sub>B</sub> = 1.0mA
Conector-Emitter Saturation Voltage	VCE(SAT)			0.20		$I_C = 50mA$ , $I_B = 5.0mA$
Base-Emitter Saturation Voltage	V <sub>BE(SAT)</sub>	_		1.0	V	$I_C = 10mA, I_B = 1.0mA$
Base-Emilier Saturation voitage						$I_C = 50 \text{mA}, I_B = 5.0 \text{mA}$
SMALL SIGNAL CHARACTERISTICS						
Output Capacitance	C <sub>obo</sub>			6.0	pF	$V_{CB} = 10V$ , $f = 1.0MHz$ , $I_E = 0$
Small Signal Current Gain	h <sub>fe</sub>	50		250		$I_C = 1 \text{mA}, V_{CE} = 10 \text{V}, f = 1.0 \text{MHz}$
Current Gain-Bandwidth Product	f <sub>T</sub>	100		300	MHz	$I_C = 10$ mA, $V_{CE} = 10$ V, $f = 100$ MHz
Noise Figure	NF	_	_	8.0	dB	$V_{CE} = 5.0V$ , $I_C = 200\mu A$ , $R_S = 1k\Omega$ , $f = 1.0kHz$

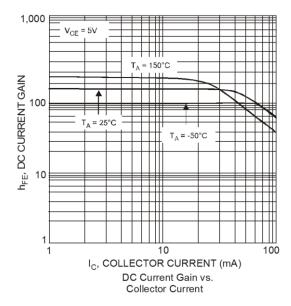
## Electrical Characteristics - PNP 5401 Section (@TA = +25°C, unless otherwise specified.)

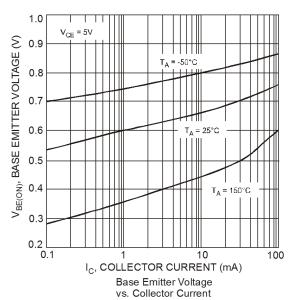
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS						
Collector-Base Breakdown Voltage	BV <sub>CBO</sub>	-160	_	_	V	$I_C = -100\mu A, I_E = 0$
Collector-Emitter Breakdown Voltage (Note 9)	BV <sub>CEO</sub>	-150	_	_	V	$I_{C} = -1 \text{mA}, I_{B} = 0$
Emitter-Base Breakdown Voltage	BV <sub>EBO</sub>	-6	_	_	V	$I_E = -10\mu A, I_C = 0$
Collector-Base Cutoff Current	1	_	_	-50	nA	V <sub>CB</sub> = -120V, I <sub>E</sub> = 0
Collector-Base Cuton Current	I <sub>CBO</sub>	_	_	-50	μA	$V_{CB} = -120V, I_E = 0, T_A = +100^{\circ}C$
Base-Emitter Cutoff Current	I <sub>EBO</sub>	_	_	-50	nA	$V_{EB} = -4V, I_C = 0$
ON CHARACTERISTICS (Note 9)						
		50		_		$I_C = -1.0 \text{mA}, V_{CE} = -5.0 \text{V}$
DC Current Gain	h <sub>FE</sub>	60	_	240	_	$I_C = -10 \text{mA}, V_{CE} = -5.0 \text{V}$
		50				$I_C = -50 \text{mA}, V_{CE} = -5.0 \text{V}$
Collector-Emitter Saturation Voltage	V			-0.20	- V	$I_C = -10mA$ , $I_B = -1.0mA$
Collector-Emitter Saturation Voltage	V <sub>CE(SAT)</sub>	_	_	-0.50		$I_C = -50 \text{mA}, I_B = -5.0 \text{mA}$
Base-Emitter Saturation Voltage	V <sub>BE(SAT)</sub>	) —	_	1.0	V	$I_C = -10 \text{mA}, I_B = -1.0 \text{mA}$
Base-Emilier Saturation voltage						$I_C = -50 \text{mA}, I_B = -5.0 \text{mA}$
SMALL SIGNAL CHARACTERISTICS						
Output Capacitance	C <sub>obo</sub>	_	_	6.0	pF	$V_{CB} = -10V$ , $f = 1.0MHz$ , $I_E = 0$
Small Signal Current Gain	h <sub>fe</sub>	40		260		$I_C = -1mA$ , $V_{CE} = -10V$ , $f = 1.0MHz$
Current Gain-Bandwidth Product	f⊤	100	_	300	MHz	$I_C = -10mA$ , $V_{CE} = -10V$ , $f = 100MHz$
Noise Figure	NF	_	_	8.0	dB	$V_{CE}$ = -5.0V, $I_C$ = -200 $\mu$ A, $R_S$ = 1 $\Omega$ , $f$ = 1.0kHz

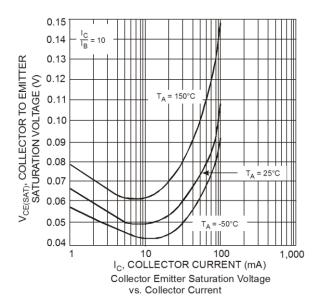
Note: 9. Measured under pulsed conditions. Pulse width  $\leq 300 \mu s.$  Duty cycle  $\leq 2\%.$ 

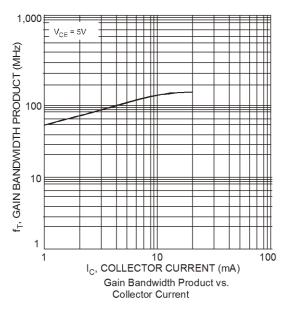


#### Typical Electrical Characteristics - NPN 5551 Section (@TA = +25°C, unless otherwise specified.)



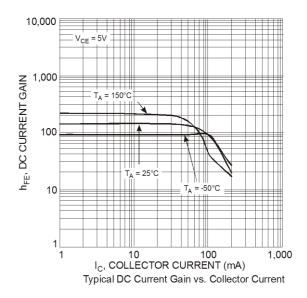


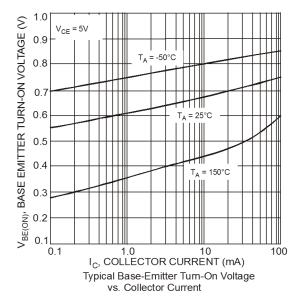


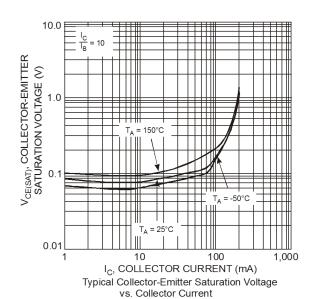


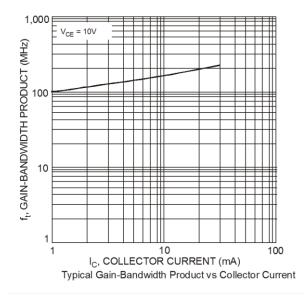


#### Typical Electrical Characteristics – PNP 5401 Section (@T<sub>A</sub> = +25°C, unless otherwise specified.)





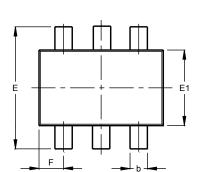


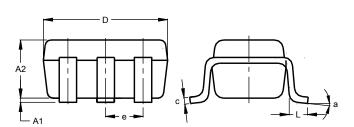




### **Package Outline Dimensions**

Please see http://www.diodes.com/package-outlines.html for the latest version.





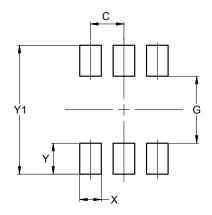
SOT363						
Dim	Min	Max	Тур			
A1	0.00	0.10	0.05			
A2	0.90	1.00	0.95			
b	0.10	0.30	0.25			
С	0.10	0.22	0.11			
D	1.80	2.20	2.15			
Е	2.00	2.20	2.10			
E1	1.15	1.35	1.30			
е	0.650 BSC					
F	0.40	0.45	0.425			
L	0.25	0.40	0.30			
а	0°	8°				
All Dimensions in mm						

#### **Suggested Pad Layout**

Please see http://www.diodes.com/package-outlines.html for the latest version.

#### **SOT363**

**SOT363** 



Dimensions	Value (in mm)			
С	0.650			
G	1.300			
Х	0.420			
Υ	0.600			
V1	2 500			

**Note:** For high voltage applications, the appropriate industry sector guidelines should be considered with regards to creepage and clearance distances between device Terminals and PCB tracking.



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